NSN 5961-01-159-5815

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View Online at https://aerobasegroup.com/nsn/5961-01-159-5815 **Inclosure Material:** Metal **Overall Length:** Between 6.223 inches and 7.255 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-9 **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 1.443 inches **Thread Size:** 0.750 inches **Criticality Code Justification:** Zzzy **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1000.0 repetitive peak reverse voltage and 800.0 reverse voltage, dc and 1200.0 nonrepetitive peak reverse voltage **Current Rating Per Characteristic:** 400.00 amperes forward current, average of standard range and 30.00 milliamperes forward current, average nanoamperes **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** Item must comply with requirements of defense supply center columbus production standard no. Lo3309; junction pattern arrangement: pn **Thread Series Designator: Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Reference Number Differentiating Characteristics:** Areference number differentiating material will be in accordance with naval inventory control point activity hx quality control. Manufacturing and testing specifications available at the dla icp Shelf Life:

No

N/a

Unit Of Measure:

Demilitarization:

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